CPI Electron Device Business - SSPA

The PTS10224 X-band GaN SSPA delivers greater than 300 W min. at up to 15% duty. The standard output connector is N-type female. Two models are available: one runs off a 40 V supply and the other at 50 V, the latter offering the best overall efficiency and output power typically in excess of 400 W.

CPI EDB's X-band SSPA employs gallium nitride (GaN) power transistors giving state-of-the-art power performance with a power-to-volume ratio.

This high-power amplifier (HPA) is well suited to a range of radar applications, enabling our customers to use compact and reliable SSPA technology instead of the incumbent traveling-wave tube amplifiers (TWTAs).

CPI EDB's high-power microwave amplifiers are continuously being improved, so please contact us for the latest specification as it is subject to change without notice.

Contact us at ElectronDevices@cpi-edb.com or call us at +44 (0)20 8573 5555



The PTS10224 SSPA - 8.5 to 9.6 GHz

FEATURES:

- Frequency: 8.5 9.6 GHz
- Output power: Typically 400 W (300 W min)
- Duty cycle: 15% max
- Saturated power gain: 55 dB nominal
- VSWR: 3:1 max

RENEFITS.

- GaN based
- Versatile
- Compact & reliable

APPLICATIONS

- Land
- Naval
- Airborne



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Frequency range	8.5 to 9.6 GHz
RF output power	Typically 400 W
(Saturated)	(300 W minimum) Electrical
	performance specified at 40 V,
20	°C and into terminating VSWR
	<1.3:1 unless otherwise stated
Output power -	± 1 dB deviation from medium
variation (Psat)	power across the band
RF input power	0 dBm ± 1 dBm
Saturated power ga	in 55 dB nominal
Pulse droop	0.8 dB maximum,
(on 100 µs pulse)	0.7 dB typical
Output phase conti	rol 5.625 deg nominal
resolution	Internal 6-bit phase shifter
HPA turn-on time	200 ns nominal measured
(from standby)	between 10 % and 90 %
	points
RF gating pulse	0.5 μs minimum
(min)	(shorter time feasible
	but not specified)
Pulse rise / Fall time	50 ns nominal
Harmonics	-50 dBc max
Spurious	-55 dBc max
Duty cycle	Maximum 15 % duty. Not to
	be exceeded with any pulse
	width, or damage may occur
PRI	13.3 µs at minimum pulse
	width only. Constrained by
	duty cycle

Termination return	17.7 dB minimum to	
loss	achieve specified	
	performance.	
Worst case load VSWR	3:1 maximum. Not to be	
	exceeded or damage may	
O	occur at high power output	
Internal protection agains		
rev	erse power is not included	

Prime Power Requirements

Prime power	+40 Vdc.
Power supply variation	+0.5 V maximum
Mean DC current	8.0 A maximum
	At maximum 15 % duty
Power added efficiency @	20 % typical
15 % duty	

Connectors

Primary power input	Hybrid, D-sub 17 pin
connector	female. NorComp
	680M17W2203L401
RF input connector	SMA Female
RF output connector	N Type Female

Operating Modes

STANDBY	HPA enabled/ disabled with "RF_
	ENABLE"TTL or 3.3V LVCMOS
	Signal High = Enabled
PULSED	Pulsed RF On, will amplify any CW
	or nested RF signal present at RF
	Input when "RF_GATE" signal is
	applied



I/O Communications

Alarm (output)

Alarm signal (3.3 V LVCMOS-Low) for any alarm state.

Connect "Alarm" (externally) to "RF_Enable" to auto-disable HPA.

Can be hard wired on request

Phase control

Control of internal 6-bit phase shifter via I2 C for phase matching

I2 C (at 3.3V)

I2 C bus: (SDA/SCL/Gnd)

monitoring of drain voltage and GaN drain currents in output stage and internal temperature. Look-up table provides addresses and cal factors

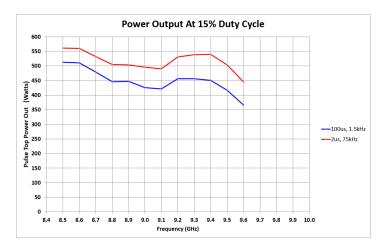
Mechanical

Mechanical outline 197 x 150 x 30 mm

excluding connectors and

fixings

Weight 1.5 kg nominal



Typlical power performance

Finish	Chemica	I conversion MIL-DTL-5541F
	Type	II /Surtec 650 or Iridite NCP
Markings/l	_abels	Type number
		Model number

Model number
Serial number
Connector ident
RF hazard warning
Hot surface warning
Anti-static warning

Environmental

Temperature (operating)	0 °C to + 60 °C
Operating humidity	Non-condensing
level	atmosphere.

EMC performance

It is expected that the customer using the SSPA will use an appropriate filtering network placed between this unit's main RF output and the antenna used in their system, to ensure compliance with MIL STD-461F



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